

Technical documentation





**TPIC1021** ZHCSQ23E - OCTOBER 2004 - REVISED MAY 2022

# TPIC1021 LIN 物理接口

# 1 特性

- 符合 LIN 物理层规范修订版本 2.1,并符合适用于 LIN 的 SAEJ2602 推荐实践要求
- LIN 总线速度高达 20kbps
- LIN 引脚提供 12kV (人体放电模型) ESD 保护 ٠
- LIN 引脚可处理 40V 至 40V 的电压 •
- 可在汽车环境中耐受瞬态损伤 (ISO 7637)
- 7V 至 27V 的直流电源工作电压范围
- 两种工作模式:正常模式和低功耗(睡眠)模式
- 低功耗模式下,电流消耗低
- 可通过 LIN 总线、唤醒输入 ( 外部开关 ) 或主机 **MCU** 唤醒
- 使用 5V 或者 3.3V I/O 引脚连接到 MCU
- TXD 引脚上提供显性状态超时保护
- RXD 引脚上提供唤醒请求功能
- 使用 INH 引脚控制外部稳压器 ٠
- 集成上拉电阻器和串联二极管适用于 LIN 响应器应 • 用
- 低 EME(电磁辐射)、高 EMI(电磁抗扰度)
- 针对电池短路或接地短路提供总线端子短路保护
- 具有热保护功能
- 系统级接地断开失效防护
- 系统级接地漂移运行
- 未供电节点不会干扰网络

## 2 应用

- 工业感应 ٠
- 白色家电分布式控制

## 3 说明

TPIC1021 是 LIN (本地互连网络)物理接口,集成了 具有唤醒和保护功能的串行收发器。LIN 总线为单线制 双向总线,通常用于低速车载网络,波特率范围为 2.4-20kbps。

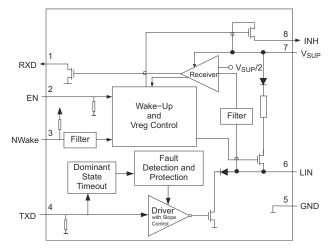
LIN 总线有两个逻辑值:显性状态(电压接近接地值) 表示逻辑值 0, 而隐性状态(电压接近电池值)表示逻 辑值 **1**。

在隐性状态下, LIN 总线由 TPIC1021 内部上拉电阻器 (30kΩ)和串联二极管拉高,因此响应器应用无需外部 上拉元件。指挥器应用需要外部上拉电阻器 (1kΩ) 及 串联二极管。

器件信息

器件型号	封装 <sup>(1)</sup>	封装尺寸(标称值)		
TPIC1021	SOIC (8)	4.90mm × 3.91mm		

如需了解所有可用封装,请参阅数据表末尾的可订购产品附 (1) 录。



功能方框图





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# **4 Revision History**

C	hanges from Revision D (June 2015) to Revision E (May 2022)	Page
•	将"特性"从"符合修订版本 2.0"更改为"符合修订版本 2.1"	1
•	将提到的所有旧术语实例更改为"指挥官"和"响应者"	1
•	将 <i>说明(续)</i> 中的"LIN物理层规范修订版本 2.0"更改为"LIN物理层规范修订版本 2.1"	3
•	Added: (LIN 2.1 compatible) to Note 2 of the Timing Requirements	6
•	Changed paragraph three in the Transmitter Characteristics section	8
•	Changed three instances of "IHN" to "INH" in 图 8-1	10
	-	

### Changes from Revision C (July 2005) to Revision D (June 2015)

Page

添加了引脚配置和功能部分、ESD等级表、特性说明部分、器件功能模式、应用和实施部分、电源相关建议部分、布局部分、器件和文档支持部分以及机械、封装和可订购信息部分......1



# 5 说明(续)

如 LIN 物理层规范修订版本 2.1 中所述,借助具有控制功能的限流波形整形低侧驱动器,TPIC1021 将 TXD 引脚上的 LIN 协议输出数据流转换为 LIN 总线信号。接收器转换 LIN 总线上的数据流,然后通过 RXD 引脚输出数据流。

在低功耗模式下,即使唤醒电路保持工作状态,TPIC1021 也需要非常低的静态电流,从而支持通过 LIN 总线进行远程唤醒,或者通过 NWake 或 EN 引脚进行本地唤醒。

**TPIC1021**旨在用于恶劣的汽车环境。该器件可处理从 40V 向下至接地的 LIN 总线电压摆幅,并且可在 -40V 的电压下运行。该器件还可在接地漂移或电源电压断开的情况下防止反馈电流经 LIN 流向电源输入。它还具有欠压、过热和接地失效保护功能。如果发生故障,输出会立即关断,并在排除故障之前一直保持关断状态。

## **6** Pin Configuration and Functions

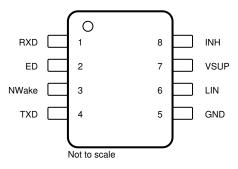


图 6-1. D Package, 8-Pin SOIC

#### 表 6-1. Pin Functions

	PIN	TYPE	DESCRIPTION
NO.	NAME	O         RXD output (open drain) pin interface reporting state of LIN bus voltage	
1	RXD	0	RXD output (open drain) pin interface reporting state of LIN bus voltage
2	ED	I	Enable input pin
3	NWake	I	High voltage input pin for device wake up
4	TXD	I	TXD input pin interface to control state of LIN output
5	GND	I	Ground connection
6	LIN	I/O	LIN bus pin single wire transmitter and receiver
7	V <sub>SUP</sub>	Supply	Device supply pin (connected to battery in series with external reverse blocking diode)
8	INH	0	Inhibit pin controls external voltage regulator with inhibit input



# **7** Specifications

## 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>SUP</sub> <sup>(2)</sup>	Supply line supply voltage	Continuous	0	27	V
VSUP (-)	Supply line supply voltage	Transient	0	40	V
	NWake DC and transient input voltage (through 33-	kΩ serial resistor)	- 1	40	V
	Logic pin input voltage (RXD, TXD, EN)		- 0.3	5.5	V
	LIN DC input voltage		- 40	40	V
T <sub>A</sub>	Operational free-air temperature		- 40	125	°C
TJ	Junction temperature		- 40	150	°C
	Thermal shutdown			200	°C
	Thermal shutdown hysteresis			25	°C
T <sub>stg</sub>	Storage temperature range		- 40	165	°C

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under #7.3 is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values are with respect to GND.

## 7.2 ESD Ratings

				VALUE	UNIT
V(ESD)         Electrostatic discharge         Human body model (HBM), per ANSI/ESDA/JEDEC         LIN pin NWake pin           Machine model <sup>(3)</sup> All other pins           Machine model <sup>(3)</sup> LIN and NWake pins           All other pins	±12000				
			NWake pin	±9000	
V <sub>(ESD)</sub>	Electrostatic discharge		All other pins	±12000	V
		Machine model <sup>(3)</sup>	LIN and NWake pins	±400	
			All other pins	±200	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) The human body model is a 100-pF capacitor discharged through a 1.5-kΩ resistor into each pin.

(3) The machine model is a 200-pF capacitor through a 10-Ω resistor and a 0.75-µH coil.

## 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
T <sub>SUP</sub>	Supply voltage	7		27	V
T <sub>AMB</sub>	Ambient temperature	- 40		125	°C

## 7.4 Thermal Information

		TPIC1021	
	THERMAL METRIC <sup>(1)</sup>	D (SOIC)	UNIT
		8 PINS	
R <sub>0 JA</sub>	Junction-to-ambient thermal resistance	145	°C/W
R <sub>0</sub> JC(top)	Junction-to-case (top) thermal resistance	61.9	°C/W
R <sub>0 JB</sub>	Junction-to-board thermal resistance	55.5	°C/W
ΨJT	Junction-to-top characterization parameter	14.3	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	55	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.



## 7.5 Electrical Characteristics

 $V_{SUP}$  = 7 V to 27 V,  $T_A$  = -40°C to 125°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
SUPP	LY					
	Operational supply voltage <sup>(2)</sup>		7	14	27	V
	Nominal supply line voltage <sup>(2)</sup>		7	14	18	V
	V <sub>SUP</sub> undervoltage threshold <sup>(2)</sup>			4.5		V
		Normal Mode, EN = 1, Bus dominant (total bus load > 500 $\Omega$ ) <sup>(3)</sup>		1.2	2.5	mA
		Standby Mode, EN = 0, Bus dominant (total bus load > 500 $\Omega$ ) <sup>(3)</sup>		1	2.1	mA
	Supply Current	Normal Mode, EN = 1, Bus recessive		300	500	μA
I <sub>CC</sub>	Supply Current	Standby Mode, EN = 0, Bus recessive		300	500	μA
		Low Power Mode, EN = 0, $V_{SUP}$ < 14 V, NWake = $V_{SUP}$ , LIN = $V_{SUP}$		20	50	μA
		Low Power Mode, EN = 0, 14 V < $V_{SUP}$ < 27 V, NWake = $V_{SUP}$ , LIN = $V_{SUP}$		50	100	μA
RXD (	DUTPUT PIN					
Vo	Output voltage		-0.3		5.5	V
I <sub>OL</sub>	Low-level output current, open drain	LIN = 0 V, RXD = 0.4 V	3.5			mA
I <sub>IKG</sub>	Leakage current, high-level	LIN = V <sub>SUP</sub> , RXD = 5 V	-5	0	5	μA
TXD II	NPUT PIN		I		I	
VIL	Low-level input voltage <sup>(2)</sup>		-0.3		0.8	V
V <sub>IH</sub>	High-level input voltage <sup>(2)</sup>		2		5.5	V
V <sub>IT</sub>	Input threshold hysteresis voltage <sup>(2)</sup>		30		500	mV
	Pull-down resistor		125	350	800	kΩ
IIL	Low-level input current	TXD = 0	-5	0	5	μA
LIN PI	N (Referenced to V <sub>SUP</sub> )	1				
V <sub>OH</sub>	High-level output voltage <sup>(2)</sup>	LIN recessive, TXD = High, I <sub>O</sub> = 0 mA	V <sub>SUP</sub> -1V			V
V <sub>OL</sub>	Low-level output voltage <sup>(2)</sup>	LIN dominant, TXD = Low, I <sub>O</sub> = 40 mA	0		0.2×V <sub>SUP</sub>	V
	Pull-up resistor to V <sub>SUP</sub>		20	30	60	kΩ
IL	Limiting current	TXD = Low	50	150	250	mA
I <sub>IKG</sub>	Leakage current	LIN = V <sub>SUP</sub>	-5	0	5	μA
V <sub>IL</sub>	Low-level input voltage <sup>(2)</sup>	LIN dominant	0×V <sub>SUP</sub>		0.4×V <sub>SUP</sub>	V
VIH	High-level input voltage <sup>(2)</sup>	LIN recessive	0.6×V <sub>SUP</sub>		V <sub>SUP</sub>	V
V <sub>IT</sub>	Input threshold voltage <sup>(2)</sup>		0.4×V <sub>SUP</sub>	0.5×V <sub>SUP</sub>	0.6×V <sub>SUP</sub>	V
V <sub>hys</sub>	Hysteresis voltage <sup>(2)</sup>		0.05×V <sub>SUP</sub>		0.175×V <sub>SUP</sub>	V
V <sub>IL</sub>	Low-level input voltage for wake- up <sup>(2)</sup>		0		0.4×V <sub>SUP</sub>	V
EN PI	N				1	
V <sub>IL</sub>	Low-level input voltage <sup>(2)</sup>		-0.3		0.8	V
VIH	High-level input voltage <sup>(2)</sup>		2		5.5	V
V <sub>hys</sub>	Hysteresis voltage <sup>(2)</sup>		30		500	mV
	Pull-down resistor		125	350	800	kΩ
	Low-level input current	EN = 0 V	-5	0	5	



## 7.5 Electrical Characteristics (continued)

 $V_{SUP}$  = 7 V to 27 V,  $T_A$  = -40°C to 125°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
INH P	IN	I			I	
Vo	DC output voltage	Transient voltage	-0.3		V <sub>SUP</sub> +0.3	V
I <sub>O</sub>	Output current		-50		2	mA
R <sub>on</sub>	On state resistance	Between V <sub>SUP</sub> and INH, INH = 2 mA drive, Normal or Standby Mode	25	40	100	Ω
I <sub>IKG</sub>	Leakage current	Low Power mode, 0 < INH < V <sub>SUP</sub>	-5	0	5	μA
NWak	e PIN					
VIL	Low-level input voltage <sup>(2)</sup>		-0.3		V <sub>SUP</sub> -3.3	V
V <sub>IH</sub>	High-level input voltage <sup>(2)</sup>		V <sub>SUP</sub> -1		V <sub>SUP</sub> +0.3	V
	Pull-up current	NWake = 0 V	-40	-10	-4	μA
I <sub>IKG</sub>	Leakage current	V <sub>SUP</sub> = NWake	-5	0	5	μA
THER	MAL SHUTDOWN		1		1	
	Shutdown junction thermal temperature			185		°C

(1) Typical values are given for  $V_{SUP} = 14 \text{ V}$  at 25°C.

(2) All voltages are defined with respect to ground; positive currents flow into the TPIC1021 device.

(3) In the dominant state the supply current increases as the supply voltage increases due to the integrated LIN responder termination resistance. At higher voltages the majority of supply current is through the termination resistance. The minimum resistance of the LIN responder termination is  $20 \text{ k}\Omega$  so the maximum supply current attributed to the termination is:  $I_{SUP (dom) max termination} \approx (V_{SUP} - (V_{LIN_Dominant}+0.7 \text{ V}) / 20 \text{ k}\Omega$ .

			MIN	NOM	MAX	UNIT
D1	Duty cycle 1 <sup>(1) (2)</sup>	$\begin{array}{l} TH_{REC(max)} = 0.744 \times V_{SUP}, \ TH_{DOM(max)} = 0.581 \times V_{SUP}, \ V_{SUP} \\ = 7.0 \ V \ to \ 18 \ V, \ t_{BIT} = 50 \ \mu s \ (20 \ kbps), \ See \ \fbox{7-1} \end{array}$	0.396			
D2	Duty cycle 2 <sup>(1) (2)</sup>	$\begin{array}{l} {\sf TH}_{\sf REC(max)} = 0.284 \times {\sf V}_{\sf SUP}, \; {\sf TH}_{\sf DOM(max)} = 0.422 \times {\sf V}_{\sf SUP}, \; {\sf V}_{\sf SUP} \\ = 7.6 \; {\sf V} \; to \; 18 \; {\sf V}, \; t_{\sf BIT} = 50 \; {\sf \mu s} \; (20 \; {\sf kbps}), \; {\sf See} \; \fbox{$$ 7-1$} \end{array}$			0.581	
D3	Duty cycle 3 <sup>(1)</sup> (2)	TH <sub>REC(max)</sub> = 0.778×V <sub>SUP</sub> , TH <sub>DOM(max)</sub> = 0.616×V <sub>SUP</sub> , V <sub>SUP</sub> = 7.0 V to 18 V, t <sub>BIT</sub> = 96 µs (10.4 kbps), See ⊠ 7-1	0.417			
D4	Duty cycle $4^{(1)}$ (2)	TH <sub>REC(max)</sub> = 0.251×V <sub>SUP</sub> , TH <sub>DOM(max)</sub> = 0.389×V <sub>SUP</sub> , V <sub>SUP</sub> = 7.6 V to 18 V, t <sub>BIT</sub> = 96 µs (10.4 kbps), See ⊠ 7-1			0.590	
t <sub>rx_pdr</sub>	Receiver rising propagation delay time	R <sub>L</sub> = 2.4 kΩ, C <sub>L</sub> = 20 pF, See 图 7-1			6	μs
t <sub>rx_pdf</sub>	Receiver rising propagation delay time	R <sub>L</sub> = 2.4 kΩ, C <sub>L</sub> = 20 pF, See   7-1			6	μs
t <sub>rx_sym</sub>	Symmetry of receiver propagation delay time (rising edge)	with respect to falling edge, See 图 7-1	- 2		2	μs
t <sub>NWake</sub>	NWake filter time for local wake-up	See 图 7-1	25	50	100	μs
t <sub>LINBUS</sub>	LIN wake-up filter time (dominant time for wake-up via LIN bus)	See   7-1	25	50	100	μs
t <sub>DST</sub>	Dominant state timeout <sup>(3)</sup>	See 图 7-1	6	9	14	ms

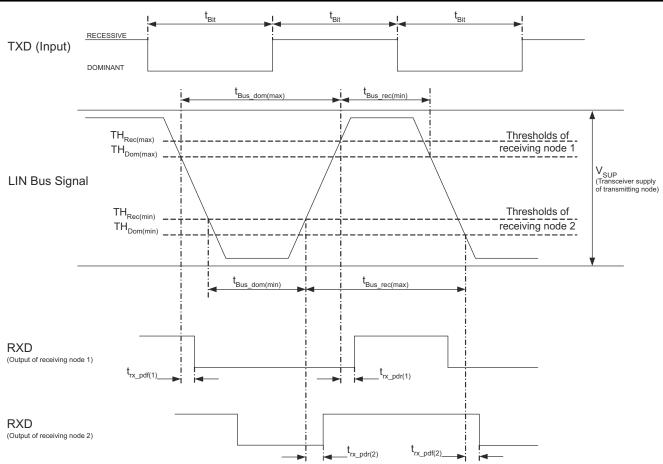
## 7.6 Timing Requirements

(1) Duty cycle =  $t_{BUS\_rec(min)}/(2 \times t_{BIT})$ 

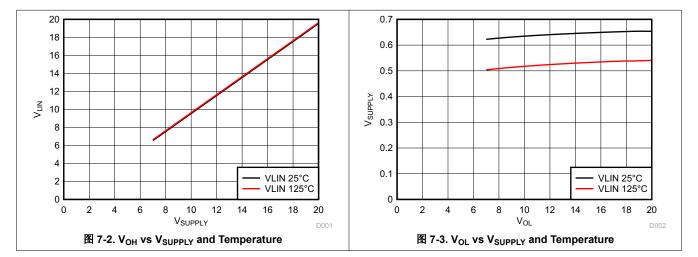
(2) Duty Cycles: LIN Driver bus load conditions (CLINBUS, RLINBUS): Load1 = 1 nF, 1 kΩ; Load2 = 6.8 nF, 660 Ω; Load3 = 10 nF, 500 Ω. Duty Cycles 3 and 4 are defined for 10.4 kbps operation. The TPIC1021 also meets these lower speed requirements, while it is capable of the higher speed 20.0 kbps operation as specified by Duty Cycles 1 and 2. SAEJ2602 derives propagation delay equations from the LIN 2.0 duty cycle definitions (LIN 2.1 compatible), for details please refer to the SAEJ2602 specification.

(3) Dominant state timeout will limit the minimum data rate to 2.4 kbps.









## 7.7 Typical Characteristics

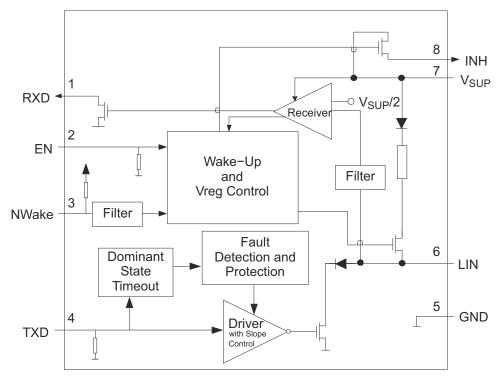


## 8 Detailed Description

## 8.1 Overview

The TPIC1021 is a LIN (Local Interconnect Network) physical layer transceiver which integrates a serial transceiver with wake up and protection features. The LIN bus is a single wire, bi-directional bus that typically is used in low speed in vehicle networks with data rates that range from 2.4 kbps to 20 kbps.

### 8.2 Functional Block Diagram



# 8.3 Feature Description

## 8.3.1 LIN Bus Pin

This I/O pin is the single-wire LIN bus transmitter and receiver.

#### 8.3.1.1 Transmitter Characteristics

The driver is a low side transistor with internal current limitation and thermal shutdown. There is an internal 30k $\Omega$  pull-up resistor with a serial diode structure to V<sub>sup</sub> so no external pull-up components are required for LIN responder mode applications. An external pull-up resistor of 1 k $\Omega$  plus a series diode to V<sub>sup</sub> must be added when the device is used for commander node applications.

Voltage on the LIN pin can go from -40 V to +40 V DC without any currents other than through the pull-up resistance. There are no reverse currents from the LIN bus to supply ( $V_{sup}$ ), even in the event of a ground shift or loss of supply ( $V_{sup}$ ).

The LIN thresholds and AC parameters are up-to-date with LIN Protocol Specification Revision 2.0, and compatible with Revision 2.1.

During a thermal shut down condition the driver is disabled.

#### 8.3.1.2 Receiver Characteristics

The characteristic thresholds of the receiver are ratio-metric with the device supply pin. Typical thresholds are 50%, with a hysteresis between 5% and 17.5% of supply.



#### 8.3.2 Transmit Input Pin (TXD)

This pin is the interface to the MCU's LIN Protocol Controller or SCI/UART used to control the state of the LIN output. When TXD is low, LIN output is dominant (near ground). When TXD is high, LIN output is recessive (near battery). TXD input structure is compatible with microcontrollers with 3.3 V and 5.0 V I/O. This pin has an internal pull-down resistor.

#### 8.3.2.1 TXD Dominant State Timeout

If the TXD pin is inadvertently driven permanently low by a hardware or software application failure, the LIN bus is protected by TPIC1021' s Dominant State Timeout Timer. This timer is triggered by a falling edge on the TXD pin. If the low signal remains on the TXD pin for longer than  $t_{DST}$ , the transmitter is disabled thus allowing the LIN bus to return to the recessive state and communication to resume on the bus. The timer is reset by a rising edge on TXD pin.

#### 8.3.3 Receive Output Pin (RXD)

This pin is the interface to the LIN protocol controller or SCI/UART of the MCU, which reports the state of the LIN bus voltage. LIN recessive (near battery) is represented by a high level on RXD and LIN dominant (near ground) is represented by a low level on RXD. The RXD output structure is an open-drain output stage. This allows the TPIC1021 to be used with 3.3 V and 5 V I/O microcontrollers. If the microcontroller' s RXD pin does not have an integrated pull-up, an external pull-up resistor to the microcontroller I/O supply voltage is required.

#### 8.3.3.1 RXD Wake-up Request

When the TPIC1021 has been in low power mode and encounters a wake-up event from the LIN bus or NWake pin the RXD pin will go LOW while the device enters and remains in Standby Mode (until EN is re-asserted high and the device enters Normal Mode).

#### 8.3.4 Ground (GND)

This is the TPIC1021 device ground connection. The TPIC1021 operates with a ground shift as long as the ground shift does not reduce  $V_{SUP}$  below the minimum operating voltage. If there is a loss of ground at the ECU level, the TPIC1021 does not have a significant current consumption on the LIN pin while in the recessive state (<100 µA sourced via the LIN pin) and for the dominant state the pull-up resistor should be active.

#### 8.3.5 Enable Input Pin (EN)

The enable input pin controls the operation mode of the TPIC1021 (Normal or Low Power Mode). When enable is high, the TPIC1021 is in normal mode allowing a transmission path from TXD to LIN and from LIN to RXD. When the enable input is low, the device is put into low power (sleep) mode and there are no transmission paths. The device can enter normal operating mode only after being woken up. The enable pin has an internal pull-down resistor to ensure the device remains in low power mode even if the enable pin floats.

#### 8.3.6 NWake Input Pin (NWake)

The NWake input pin is a high-voltage input used to wake up the TPIC1021 from low power mode. NWake is usually connected to an external switch in the application. A falling edge on NWake with a low that is asserted longer than the filter time ( $t_{NWAKE}$ ) results in a local wake-up. The NWake pin provides an internal pull-up current source to  $V_{SUP}$ .

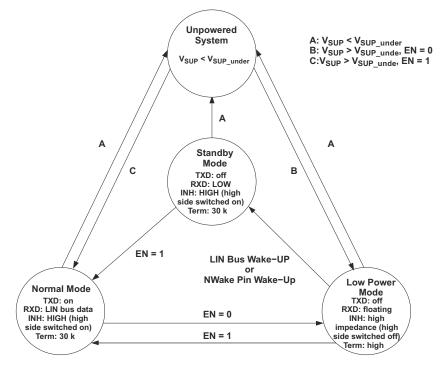
#### 8.3.7 Inhibit Output Pin (INH)

The inhibit output pin is used to control an external voltage regulator that has an inhibit input. When the TPIC1021 is in normal operating mode, the inhibit high-side switch is enabled and the external voltage regulator is activated. When TPIC1021 is in low power mode, the inhibit switch is turned off, which disables the voltage regulator. A wake-up event on for the TPIC1021 will return the INH pin to  $V_{SUP}$  level. The INH pin output current is limited to 2 mA. The INH pin can also drive an external transistor connected to an MCU interrupt input.



## 8.4 Device Functional Modes

### 8.4.1 Operating States



#### 图 8-1. Operating States Diagram

MODE	EN	EN RXD LIN BUS TERMINATION INH TRANSMITTER		COMMENTS		
Low Power	0	Floating	High impedance	High impedance	Off	
Standby	0	Low	30 k $\Omega$ (typical)	High	Off	Wake-up event detected, waiting on MCU to set EN
Normal	1	LIN bus data	30 kΩ (typical)	High	On	

#### 8.4.1.1 Normal Mode

This is the normal operational mode where the receiver and driver are active. The receiver detects the data stream on the LIN bus and outputs it on the RXD pin for the LIN controller where recessive on the LIN bus is a digital high and dominate on the LIN bus is digital low. The driver transmits input data on the TXD pin to the LIN bus.



#### 8.4.1.2 Low Power Mode

The power saving mode for the TPIC1021 and the default state after power-up (assuming EN=0). Even with the extremely low current consumption in this mode, the TPIC1021 can still wake-up from LIN bus activity, a falling edge on the NWake pin or if EN is set high. The LIN bus and NWake pins are filtered to prevent false wake-up events. The wake-up events must be active for their respective time periods: t<sub>LINBUS</sub>, t<sub>NWake</sub>.

The low power mode is entered by setting the EN pin low.

While the device is in low power mode the following conditions exist:

- The LIN bus driver is disabled and the internal LIN bus termination is switched off (to minimize power loss if LIN is short-circuited to ground).
- The normal receiver is disabled.
- The INH pin is high impedance.
- EN input, NWake input and the LIN wake-up receiver are active.

#### 8.4.1.3 Wake-Up Events

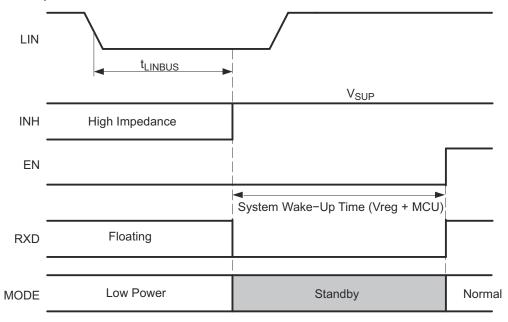
There are three ways to wake-up the TPIC1021 from Low Power Mode.

- Remote wake-up via recessive (high) to dominant (low) state transition on LIN Bus where dominant bus state
  of 50% threshold is detected. The dominant state must be held for t<sub>LINBUS</sub> filter time (to eliminate false wake
  ups from disturbances on the LIN Bus).
- Local wake-up via falling edge on NWake pin which is held low for filter time t<sub>NWake</sub> (to eliminate false wake ups from disturbances on NWake).
- · Local wake-up via EN being set high

#### 8.4.1.4 Standby Mode

This mode is entered whenever a wake-up event occurs via the LIN bus or NWake pin while the TPIC1021 is in low power mode. The LIN bus responder termination circuit and the INH pin are turned on when standby mode is entered. The application system powers up once the INH pin is driven high assuming it is using a voltage regulator connected via INH pin. Standby Mode is signaled via a low level on RXD pin.

When EN pin is set high while the TPIC1021 is in Standby Mode the device returns to Normal Mode and the normal transmission paths from TXD to LIN bus and LIN bus to RXD are turned on.



#### 图 8-2. Wake-Up Via LIN Bus Timing Diagram



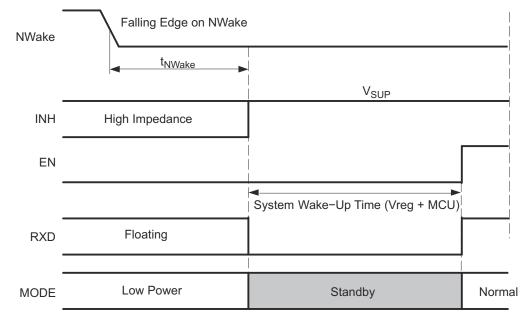


图 8-3. Wake-Up Via NWake Timing Diagram

## 8.4.2 Supply Voltage (V<sub>SUP</sub>)

This is the TPIC1021 device power supply pin. This pin is connected to the battery through an external reverse battery blocking diode. The continuous DC operating voltage range for the TPIC1021 is from 7 V to +27 V. The  $V_{SUP}$  is protected for harsh automotive conditions of up to + 40 V.

The device contains a reset circuit to avoid false bus messages during undervoltage conditions when  $V_{SUP}$  is less than  $V_{SUP\_UNDER}$ .



## 9 Application and Implementation

备注

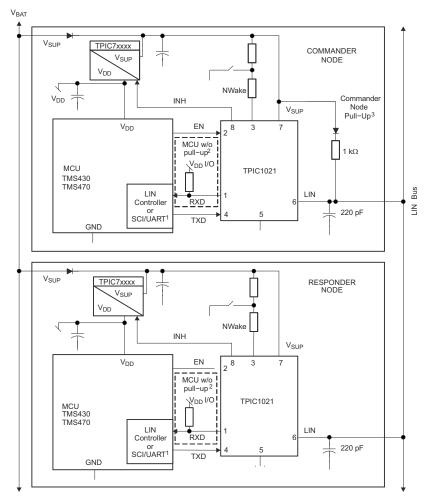
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

The TPIC1021 can be used as both a responder device and a commander device in a LIN network. It comes with the ability to support both remote wake-up requests and local wake-up requests.

#### 9.2 Typical Application

The device comes with an integrated 30-k  $\Omega$  pullup resistor and series diode for responder applications, and for commander applications an external 1-k  $\Omega$  pullup with series blocking diode can be used. A 9-1 shows the device being used in both types of applications.



A. See 1 in the #9.2.1 section

C. See 3 in the #9.2.1 section

#### 图 9-1. Typical Application Schematic

13

B. See 2 in the  $\frac{17}{9.2.1}$  section



#### 9.2.1 Design Requirements

For this design, use these requirements:

- 1. RXD on MCU or LIN Responder has internal pullup, no external pullup resistor is needed.
- 2. RXD on MCU or LIN Responder without internal pull-up, requires external pullup resistor.
- 3. Commander Node applications require an external  $1-k\Omega$  pullup resistor and serial diode.

#### 9.2.2 Detailed Design Procedure

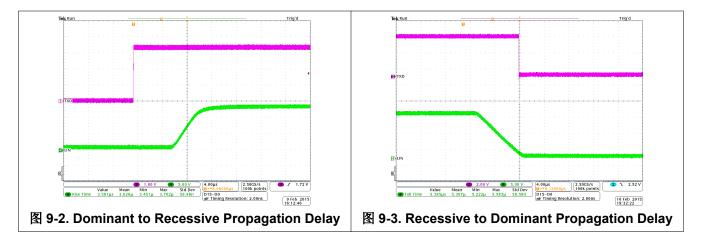
The RXD output structure is an open-drain output stage. This allows the TPIC1021 to be used with 3.3-V and 5-V I/O microcontrollers. If the RXD pin of the microcontroller does not have an integrated pull-up, an external pullup resistor to the microcontroller I/O supply voltage is required.

The  $V_{SUP}$  pin of the device should be decoupled with a 100-nF capacitor as close to the supply pin of the device as possible.

The NWAKE pin is a high voltage wake-up input to the device. If this pin is not being used it should be tied to  $V_{SUP}$ .

#### 9.2.3 Application Curves

图 9-2 and 图 9-3 show the propagation delay from the TXD pin to the LIN pin for both the recessive to dominant and dominant to recessive states under lightly loaded conditions.



#### 9.3 Power Supply Recommendations

The TPIC1021 was designed to operate directly off car battery, or any other DC supply ranging from 7 V to 27 V. A 100-nF decoupling capacitor should be placed as close to the  $V_{SUP}$  pin of the device as possible.

## 9.4 Layout

#### 9.4.1 Layout Guidelines

- Pin 1 is the RXD output of the TPIC1021. It is an open drain output and requires an external pull-up resistor in the range of 1 to 10 k Ω to function properly. If the micro-processor paired with the transceiver does not have an integrated pullup and external resistor should be placed between RXD and the regulated voltage supply for the micro-processor.
- Pin 2 is the EN input pin for the device that is used to place the device in low power sleep mode. If this feature is not used on the device, the pin should be pulled high to the regulated voltage supply of the micro-processor through a series 1-k Ω to 10-k Ω series resistor. Additionally, a series resistor may be placed on the pin to limit the current on the digital lines in the case of an overvoltage fault.
- Pin 3 is a high-voltage local wake up input pin. The device is typically externally controlled by a normally open switch tied between NWAKE and ground. When the momentary switch is pressed the NWAKE pin is pulled to ground signaling a local wake-up event. A series resistor between VBATT and the switch, and NWAKE and



the switch should be placed to limit current. If the NWAKE local wake-up feature is not used, the pin can be tied to  $V_{SUP}$  through a 1-k  $\Omega$  to 10-k  $\Omega$  pullup resistor.

- Pin 4 is the transmit input signal to the device. A series resistor can be placed to limit the input current to the device in the case of an overvoltage on this pin. Also a capacitor to ground can be placed close to the input pin of the device to filter noise.
- Pin 5 is the ground connection of the device. This pin should be tied to a ground plane through a short trace with the use of two vias to limit total return inductance.
- Pin 6 is the LIN bus connection of the device. For responder applications a 220pF bus capacitor is implemented. For commander applications an additional series resistor and blocking diode should be placed between the LIN pin and the V<sub>SUP</sub> pin.
- Pin 7 is the supply pin for the device. A 100-nF decoupling capacitor should be placed as close to the device as possible.
- Pin 8 is a high-voltage output pin that may be used to control the local power supplies. If this feature is not used the pin may be left floating.

备注

All ground and power connections should be made as short as possible and use at least two vias to minimize the total loop inductance.

#### 9.4.2 Layout Example

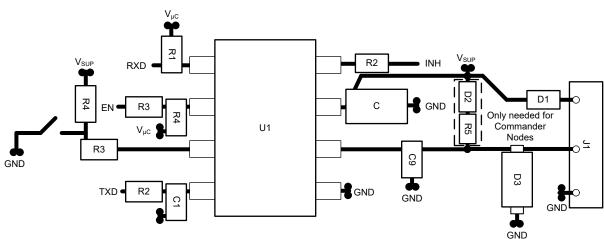


图 9-4. Layout Example



## **10 Device and Documentation Support**

### 10.1 接收文档更新通知

要接收文档更新通知,请导航至 ti.com 上的器件产品文件夹。点击*订阅更新*进行注册,即可每周接收产品信息更改摘要。有关更改的详细信息,请查看任何已修订文档中包含的修订历史记录。

### 10.2 支持资源

TI E2E<sup>™</sup> 支持论坛是工程师的重要参考资料,可直接从专家获得快速、经过验证的解答和设计帮助。搜索现有解 答或提出自己的问题可获得所需的快速设计帮助。

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### 10.3 Trademarks

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#### **10.4 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 10.5 术语表

TI 术语表 本术语表列出并解释了术语、首字母缩略词和定义。

### 11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGING INFORMATION

Orderable Device		Package Type	Package Drawing	Pins	Package Qty		Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TPIC1021D	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T1021	
TPIC1021DG4	NRND	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		T1021	
TPIC1021DR	NRND	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	T1021	
TPIC1021DRG4	NRND	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM		T1021	

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption. **Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# PACKAGE OPTION ADDENDUM

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



Texas

STRUMENTS

## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are n	ominal											
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC1021DR	R SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TPIC1021DRC	64 SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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# PACKAGE MATERIALS INFORMATION

3-Jun-2022



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC1021DR	SOIC	D	8	2500	356.0	356.0	35.0
TPIC1021DRG4	SOIC	D	8	2500	356.0	356.0	35.0

## TEXAS INSTRUMENTS

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# TUBE



# - B - Alignment groove width

#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TPIC1021D	D	SOIC	8	75	505.46	6.76	3810	4
TPIC1021D	D	SOIC	8	75	506.6	8	3940	4.32
TPIC1021DG4	D	SOIC	8	75	506.6	8	3940	4.32
TPIC1021DG4	D	SOIC	8	75	505.46	6.76	3810	4

# D0008A



# **PACKAGE OUTLINE**

# SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



#### NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



# D0008A

# **EXAMPLE BOARD LAYOUT**

# SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# D0008A

# **EXAMPLE STENCIL DESIGN**

# SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



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